Features

- Trench Power LV MOSFET Technology
- Excellent Package For Heat Dissipation
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Dual N-CHANNEL MOSFET

Maximum Ratings

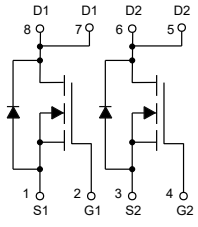
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 54°C/W Junction to Ambient(Note2)
- Thermal Resistance: 7°C/W Junction to Case

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	25	A
	T_C=100°C		15.8	
Pulsed Drain Current(Note3)		I_{DM}	100	A
Total Power Dissipation(Note4)		P_D	18	W
Single Pulsed Avalanche Energy(Note5)		E_{AS}	50	mJ

Note:

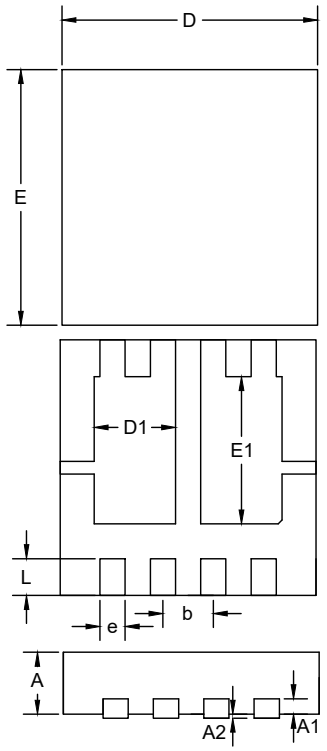
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. T_J=25°C, V_{DD}=40V, V_{GS}=10V, R_G=25Ω, L=1mH.

Internal Structure and Marking Code



pin1

DFN3333-D



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.030	0.033	0.750	0.850	
A1	0.008		0.200		TYP
A2	-	0.002	-	0.050	
D	0.128	0.132	3.250	3.350	
E	0.128	0.132	3.250	3.350	
D1	0.039	0.043	1.000	1.100	
E1	0.073	0.077	1.850	1.950	
b	0.026		0.650		BSC
e	0.012	0.014	0.300	0.350	
L	0.017	0.021	0.425	0.525	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	40			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=8A		14	18	mΩ
		V_{GS}=4.5V, I_D=4A		18	24	
Gate Resistance	R_g	f=1MHz, Open Drain		2.1		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				25	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=10A			1.2	V
Reverse Recovery Time	t_{rr}	I_S=10A,di/dt=100A/μs		17.5		ns
Reverse Recovery Charge	Q_{rr}			9.3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V,f=1MHz		940		pF
Output Capacitance	C_{oss}			113		
Reverse Transfer Capacitance	C_{rss}			102		
Total Gate Charge	Q_g	V_{DS}=20V,V_{GS}=10V,I_D=10A		24.5		nC
Gate-Source Charge	Q_{gs}			2.6		
Gate-Drain Charge	Q_{gd}			6.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=20V, V_{GS}=10V, R_G=3Ω, I_{DS}=2A		6.6		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			24.5		
Turn-Off Fall Time	t_f			6.8		

Curve Characteristics

Fig.1 - Typical Output Characteristics

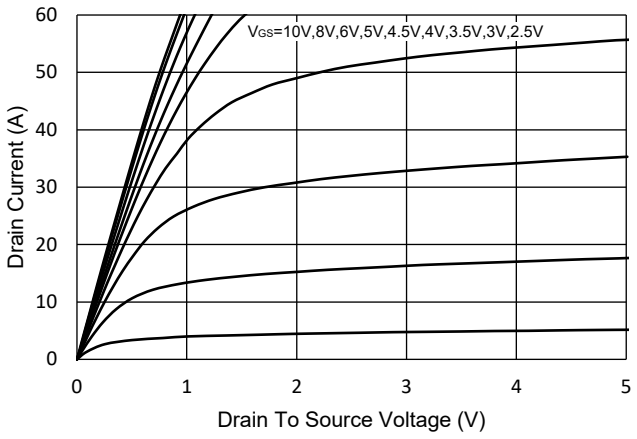


Fig.2 - Transfer Characteristic

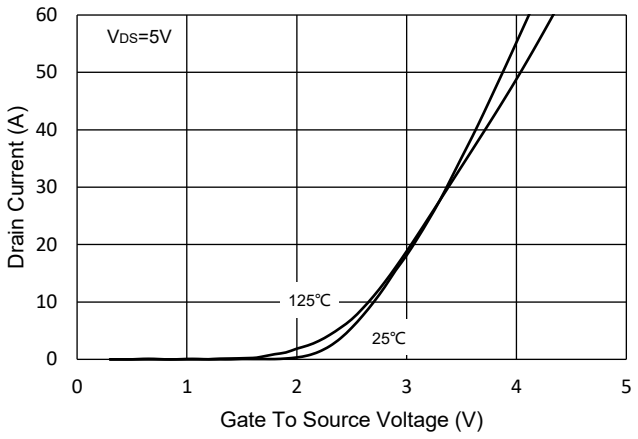


Fig.3 - $R_{DS(ON)}$ - V_{GS}

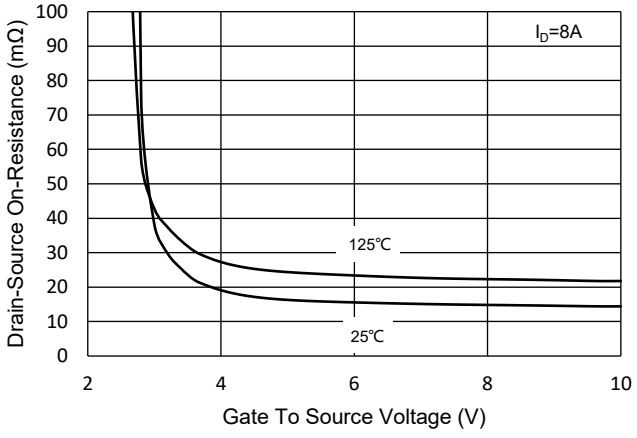


Fig.4 - $R_{DS(ON)}$ - I_D

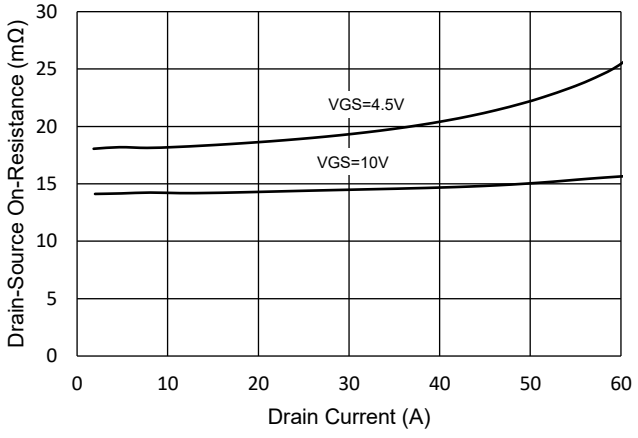


Fig.5 - Capacitance Characteristics

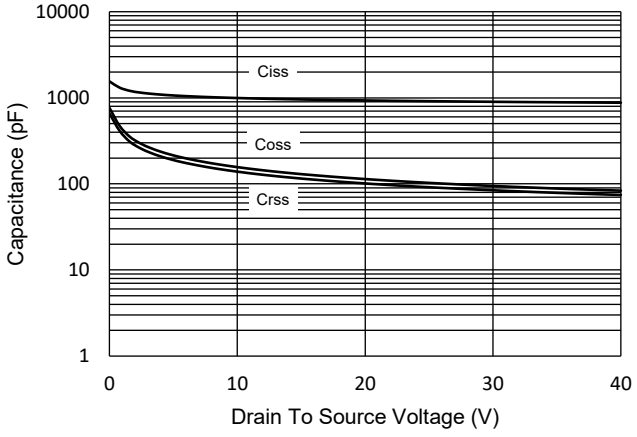
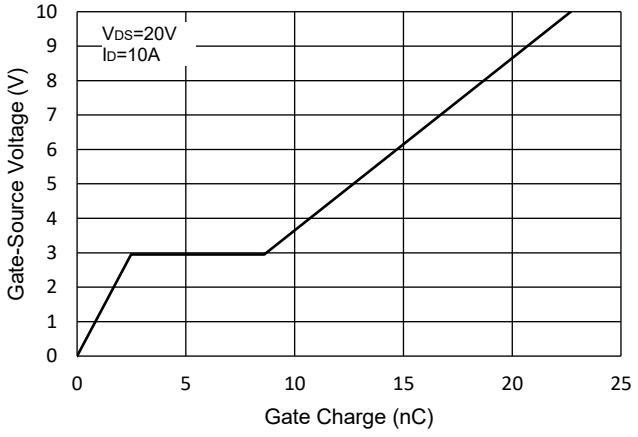


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

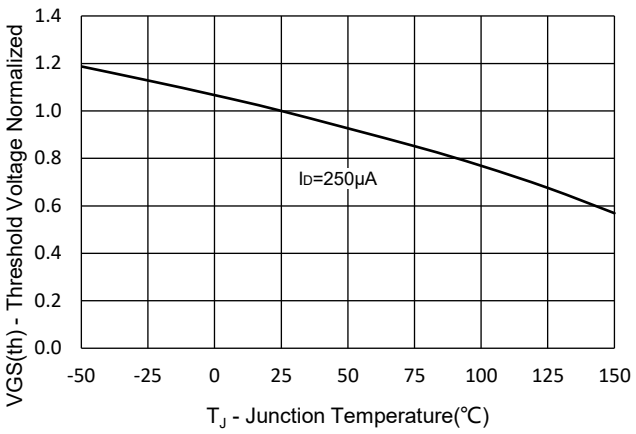


Fig.8 - Normalized On Resistance Characteristics

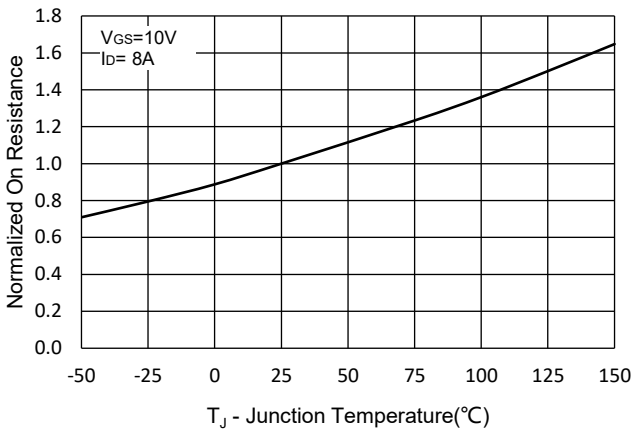


Fig.9 - I_S - V_{SD}

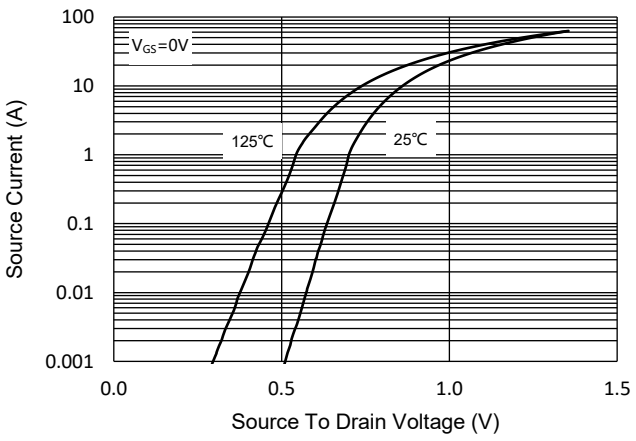


Fig.10 - Drain Current

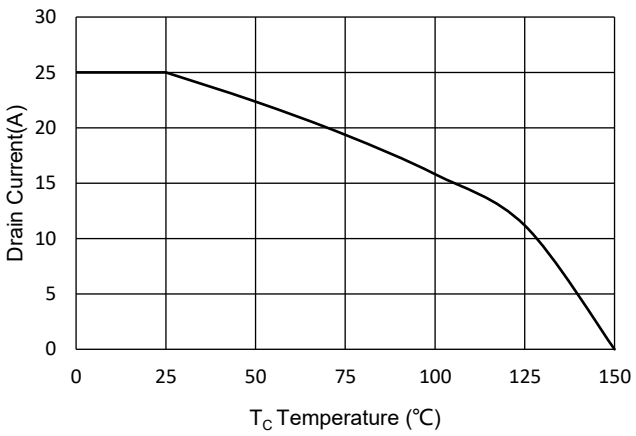
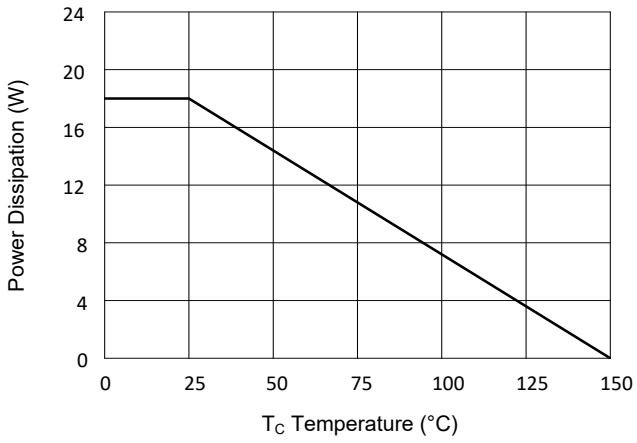


Fig.11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

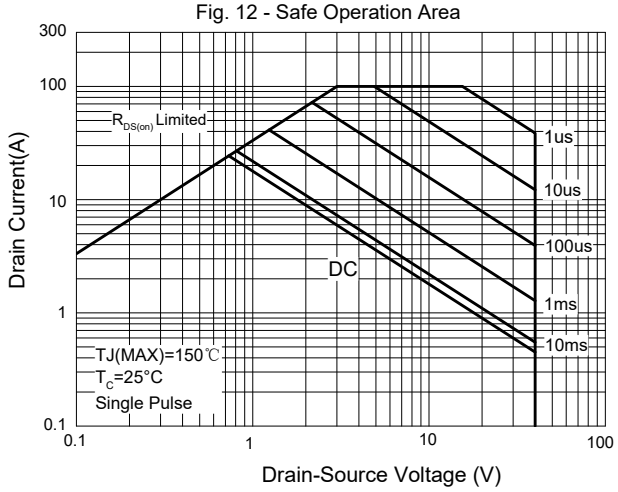
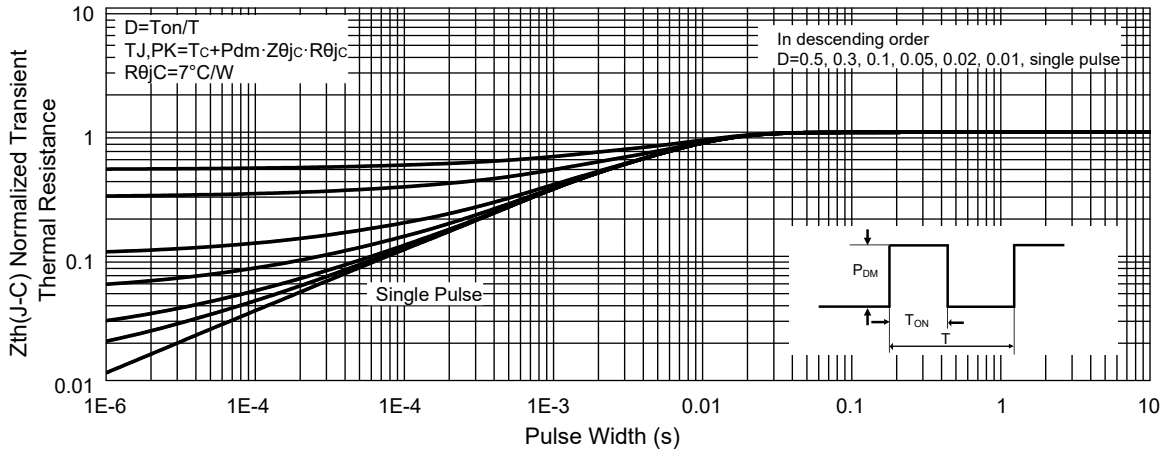


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel